

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N5400
2N5401

PNP SILICON TRANSISTOR

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5400, 2N5401 types are epoxy molded PNP Silicon Transistors designed for high voltage amplifier applications.

MAXIMUM RATINGS (T_A = 25°C)

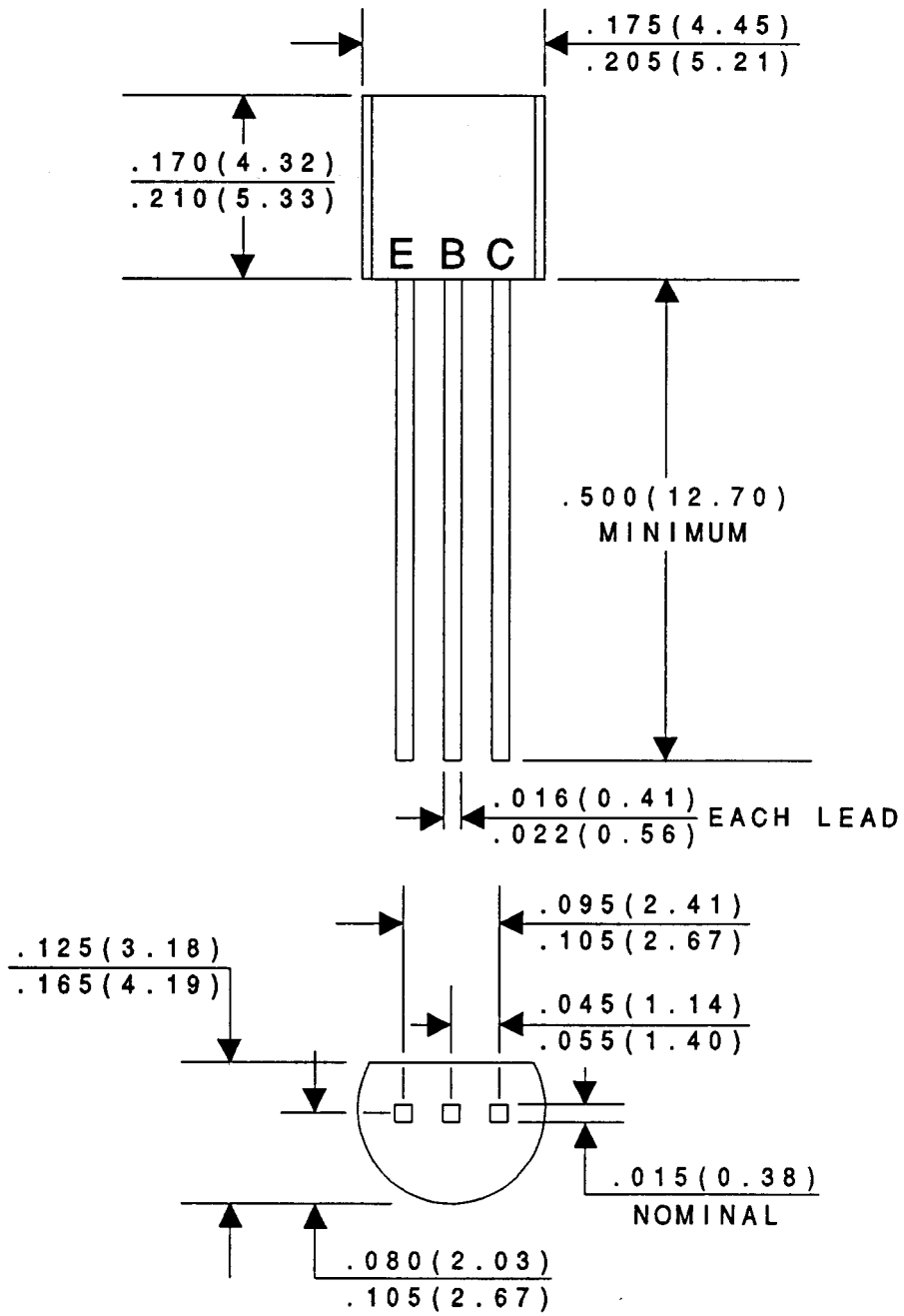
	SYMBOL	2N5400	2N5401	UNITS
Collector-Base Voltage	V _{CB0}	130	160	V
Collector-Emitter Voltage	V _{CEO}	120	150	V
Emitter-Base Voltage	V _{EBO}		5.0	V
Continuous Collector Current	I _C	600		mA
Power Dissipation	P _D		625	mW
Operating and Storage				
Junction Temperature	T _J , T _{stg}	-65 to +150		°C
Thermal Resistance	θ _{JA}	200		°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5400		2N5401		UNITS
		MIN	MAX	MIN	MAX	
I _{CB0}	V _{CB} = 100V		100		-	nA
I _{CB0}	V _{CB} = 100V, T _A = 100°C		100		-	μA
I _{CB0}	V _{CB} = 120V		-		50	nA
I _{CB0}	V _{CB} = 120V, T _A = 100°C		-		50	μA
I _{EBO}	V _{EB} = 3.0V		50		50	nA
BV _{CB0}	I _C = 100μA	130		160		V
BV _{CEO}	I _C = 1.0mA	120		150		V
BV _{EBO}	I _E = 10μA	5.0		5.0		V
V _{CE(SAT)}	I _C = 10mA, I _B = 1.0mA		0.2		0.2	V
V _{CE(SAT)}	I _C = 50mA, I _B = 5.0mA		0.5		0.5	V
V _{BE(SAT)}	I _C = 10mA, I _B = 1.0mA		1.0		1.0	V
V _{BE(SAT)}	I _C = 50mA, I _B = 5.0mA		1.0		1.0	V
h _{FE}	V _{CE} = 5.0V, I _C = 1.0mA	30		50		
h _{FE}	V _{CE} = 5.0V, I _C = 10mA	40	240	60	240	
h _{FE}	V _{CE} = 5.0V, I _C = 50mA	40		50		
f _T	V _{CE} = 10V, I _C = 10mA, f = 100MHz	100	400	100	300	MHz
C _{ob}	V _{CB} = 10V, I _E = 0, f = 1.0MHz		6.0		6.0	pF
h _{fe}	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz	30	200	40	200	
NF	V _{CE} = 5.0V, I _C = 250μA, R _S = 1kΩ, f = 10Hz to 15.7kHz		8.0		8.0	dB

(SEE REVERSE SIDE)

JEDEC TO-92 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).